TOSHIBA Field Effect Transistor Silicon P Channel MOS Type ( $L^2$ - $\pi$ -MOSV)

# **2SJ465**

# DC-DC Converter, Relay Drive and Motor Drive Applications

• 2.5-V gate drive

• Low drain-source ON-resistance :  $RDS(ON) = 0.54 \Omega \text{ (typ.)}$ 

• High forward transfer admittance :  $|Y_{fs}| = 1.7 \text{ S (typ.)}$ 

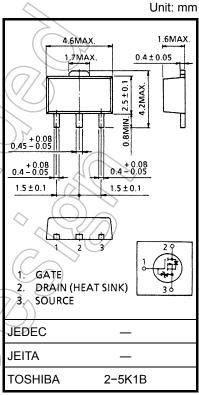
• Low leakage current :  $IDSS = -100 \mu A \text{ (max) (VDS} = -16 \text{ V)}$ 

• Enhancement mode :  $V_{th} = -0.5 \text{ to } -1.1 \text{ V}$ 

 $(V_{DS} = -10 \text{ V}, I_{D} = -200 \text{ }\mu\text{A})$ 

## Absolute Maximum Ratings (Ta = 25°C)

| Characteris             | stics                  | Symbol           | Rating     | Unit |
|-------------------------|------------------------|------------------|------------|------|
| Drain-source voltage    |                        | $V_{DSS}$        | -16        | V    |
| Drain-gate voltage (Ro  | <sub>SS</sub> = 20 kΩ) | $V_{DGR}$        | -16        | V    |
| Gate-source voltage     |                        | $V_{GSS}$        | ±8         | ∨    |
| Drain current           | DC (Note 1)            | I <sub>D</sub>   | -2         | Α    |
|                         | Pulse (Note 1)         | I <sub>DP</sub>  | -6         | (    |
| Drain power dissipation | 1                      | P <sub>D</sub>   | 0.5        | /\w  |
| Drain power dissipation | (Note 2)               | PD               | 1.5        | W    |
| Channel temperature     |                        | T <sub>ch</sub>  | 150        | °C   |
| Storage temperature ra  | inge                   | T <sub>stg</sub> | -55 to 150 | ∕\°C |



Weight: 0.05 g (typ.)

- Note 1: Ensure that the channel temperature does not exceed 150°C.
- Note 2: Mounted on a ceramic substrate (25.4 mm × 25.4 mm × 0.8 mm)
- Note 3: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### Thermal Characteristics

| Characteristics                        | Symbol                 | Max | Unit |
|----------------------------------------|------------------------|-----|------|
| Thermal resistance, channel to ambient | R <sub>th (ch-a)</sub> | 250 | °C/W |

This transistor is an electrostatic-sensitive device.

Please handle with caution.

### **Electrical Characteristics (Ta = 25°C)**

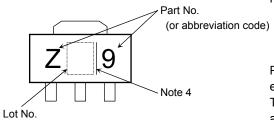
| Charac                              | cteristics    | Symbol               | Test Condition                                                            | Min                            | Тур. | Max  | Unit |
|-------------------------------------|---------------|----------------------|---------------------------------------------------------------------------|--------------------------------|------|------|------|
| Gate leakage cu                     | ırrent        | I <sub>GSS</sub>     | V <sub>GS</sub> = ±6.5 V, V <sub>DS</sub> = 0 V                           | _                              | _    | ±10  | μΑ   |
| Drain cut-off cu                    | rrent         | I <sub>DSS</sub>     | V <sub>DS</sub> = -16 V, V <sub>GS</sub> = 0 V                            | _                              | _    | -100 | μΑ   |
| Drain-source br<br>voltage          | eakdown       | V (BR) DSS           | I <sub>D</sub> = -10 mA, V <sub>GS</sub> = 0 V                            | -16                            | _    | _    | V    |
| Gate threshold v                    | oltage/       | V <sub>th</sub>      | $V_{DS} = -10 \text{ V}, I_D = -200 \mu\text{A}$                          | (-0.5                          | 1    | -1.1 | V    |
| Drain-source ON-resistance          |               | Pro (ON)             | $V_{GS} = -2.5 \text{ V}, I_D = -0.5 \text{ A}$                           |                                | 0.82 | 1.0  | Ω    |
|                                     |               | R <sub>DS</sub> (ON) | $V_{GS} = -4 \text{ V}, I_D = -1 \text{ A}$                               | $\langle \hat{\gamma} \rangle$ | 0.54 | 0.71 |      |
| Forward transfer                    | r admittance  | Y <sub>fs</sub>      | V <sub>DS</sub> = -10 V, I <sub>D</sub> = -1 A                            | 0.8                            | 1.7  | 1    | S    |
| Input capacitance                   |               | C <sub>iss</sub>     |                                                                           | > —                            | 270  | 1    |      |
| Reverse transfer capacitance        |               | C <sub>rss</sub>     | V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0 V, f = 1 MHz                 | _                              | 25   | 1    | pF   |
| Output capacitance                  |               | Coss                 | 4( >>                                                                     | _                              | 115  | /    |      |
| Switching time                      | Rise time     | t <sub>r</sub>       | V <sub>GS</sub> OV ] [ ID = -1A OVOUT                                     | _(                             | 200  | > -  |      |
|                                     | Turn-on time  | t <sub>on</sub>      | -5V R <sub>I.</sub> =8Ω                                                   |                                | 250  | _    |      |
|                                     | Fall time     | t <sub>f</sub>       | Why = 8V                                                                  | 2                              | 200  | _    | ns   |
|                                     | Turn-off time | t <sub>off</sub>     | $V_{DD} = -8V$ Duty $\leq 1\%$ , $t_{w} = 10\mu s$                        | )_                             | 500  | -    |      |
| Total gate charg<br>(Gate-source pl |               | Qg                   |                                                                           |                                | 5    | _    |      |
| Gate-source charge                  |               | Q <sub>gs</sub>      | $V_{DD} \approx -16 \text{ V}, V_{GS} = -5 \text{ V}, I_D = -2 \text{ A}$ | _                              | 3.2  | _    | nC   |
| Gate-drain ("miller") charge        |               | Qgd                  |                                                                           | _                              | 1.8  | 1    |      |

## Source-Drain Ratings and Characteristics (Ta = 25°C)

| Characteristics                           | Symbol           | Test Condition                                | Min | Тур. | Max | Unit |
|-------------------------------------------|------------------|-----------------------------------------------|-----|------|-----|------|
| Continuous drain reverse current (Note 1) | IDR              | -                                             | 1   | ı    | -2  | Α    |
| Pulse drain reverse current (Note 1)      | I <sub>DRP</sub> | _                                             |     | _    | -6  | Α    |
| Forward voltage (diode)                   | V <sub>DSF</sub> | $I_{DR} = -2 \text{ A}, V_{GS} = 0 \text{ V}$ |     | _    | 1.7 | V    |
| Reverse recovery time                     | t <sub>rr</sub>  | I <sub>DR</sub> = -2 A, V <sub>GS</sub> = 0 V | 1   | 130  | 1   | ns   |
| Reverse recovery charge                   | Qrr              | dl <sub>DR</sub> / dt = 50 A / µs             |     | 0.13 | _   | μC   |

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### Marking

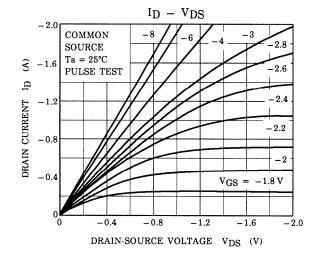


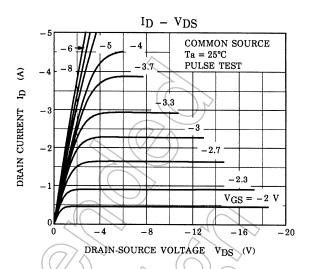
Note 4: A line to the right of a Lot No. identifies the indication of product Labels.

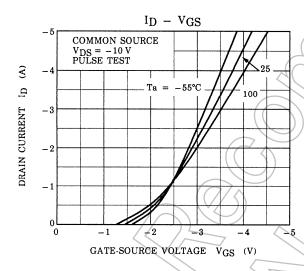
Without a line: [[Pb]]/INCLUDES > MCV

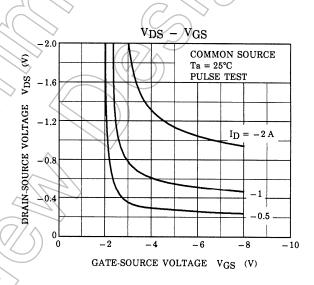
With a line: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

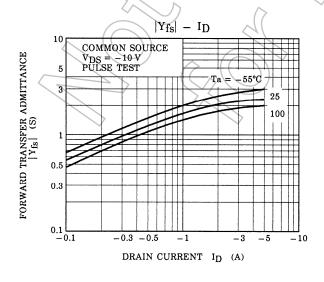
Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

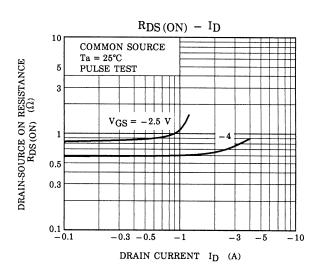


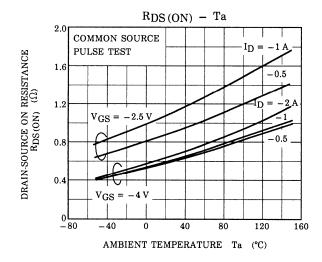


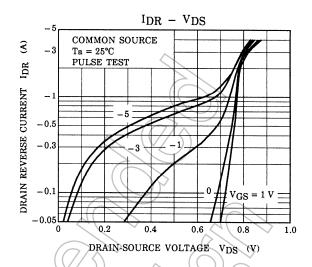


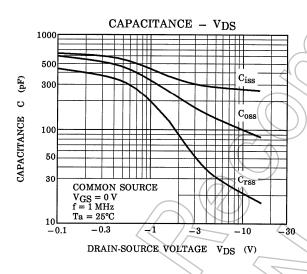


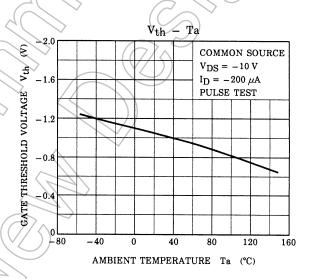


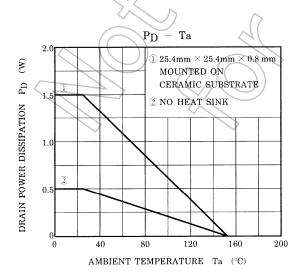


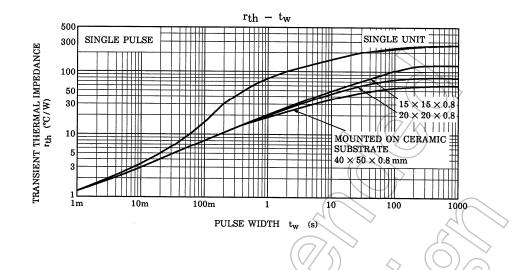


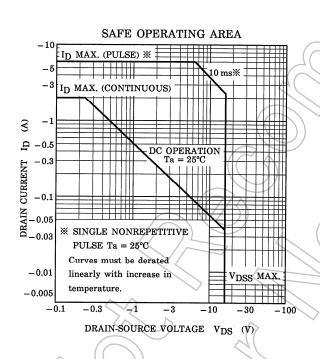












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